

**isc N-Channel MOSFET Transistor**
**15N65**
**• FEATURES**

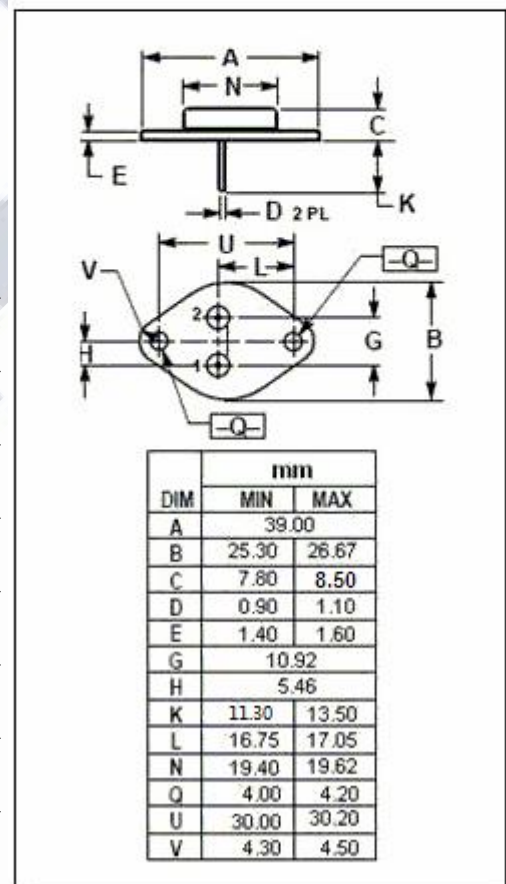
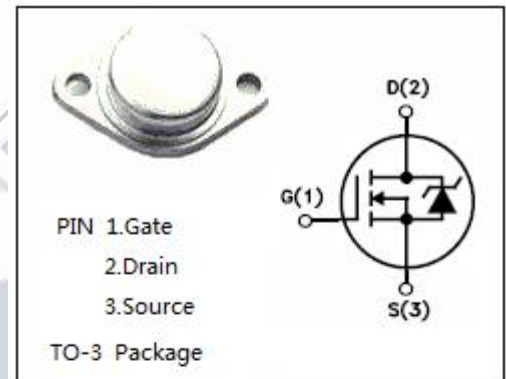
- Drain Current  $I_D = 15A @ T_C = 25^\circ C$
- Drain Source Voltage  
:  $V_{DSS} = 650V(\text{Min})$
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 0.78 \Omega (\text{Max})$
- Fast Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**• DESCRIPTION**

- Switch regulators

**• ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	650	V
$V_{GS}$	Gate-Source Voltage-Continuous	$\pm 20$	V
$I_D$	Drain Current-Continuous	15	A
$I_{DM}$	Drain Current-Single Pulsed	45	A
$P_D$	Total Dissipation @ $T_C = 25^\circ C$	250	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-55~150	$^\circ C$



**isc N-Channel MOSFET Transistor****15N65****• ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=1\text{mA}$	650			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=250\mu\text{A}$	3.0		4.5	V
$V_{SD}$	Diode Forward On-voltage	$I_S=15\text{A}; V_{GS}=0$			1.2	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=6\text{A}$			0.78	$\Omega$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS}=\pm 15\text{V}; V_{DS}=0$			$\pm 100$	nA
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=600\text{V}; V_{GS}=0$			25	$\mu\text{A}$